

L Number	Hits	Search Text	DB	Time stamp
1	1260	((insulat\$3 dielectric oxide interlayer) near (layer film)) with differ\$10 with (permittivity (dielectric near constant))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 10:40
2	303	((insulat\$3 dielectric oxide interlayer) near (layer film)) with differ\$10 with (permittivity (dielectric near constant))) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 10:24
3	16	((insulat\$3 dielectric oxide interlayer) near (layer film)) with differ\$10 with (permittivity (dielectric near constant))) and memory) and (soft near error)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 10:41
4	4539	memory and (soft near error)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 10:40
5	16	(memory and (soft near error)) and ((insulat\$3 dielectric oxide interlayer) near (layer film)) with differ\$10 with (permittivity (dielectric near constant)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 10:40
7	9	(memory same ((insulat\$3 dielectric oxide interlayer) near (layer film)) with differ\$10 with (permittivity (dielectric near constant))) and (soft near error)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 10:41
6	59	memory same ((insulat\$3 dielectric oxide interlayer) near (layer film)) with differ\$10 with (permittivity (dielectric near constant))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 11:09
8	155	memory same ((insulat\$3 dielectric oxide interlayer) near (layer film)) same differ\$10 same (permittivity (dielectric near constant))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/21 11:09